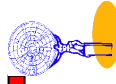


# ***ATLAS Radiation Monitoring Meeting***



*I. Mandić, ATLAS Radiation Monitor Meeting, June 27 2005, CERN*



Integrating part of the *ATLAS Radiation Monitor* will measure

- Total Ionization Dose - TID
- Non-Ionizing Energy Loss – (bulk damage in silicon)
- Thermal Neutron Fluence (in the ID)

Design of the integrating monitor in the ATLAS Inner Detector well advanced

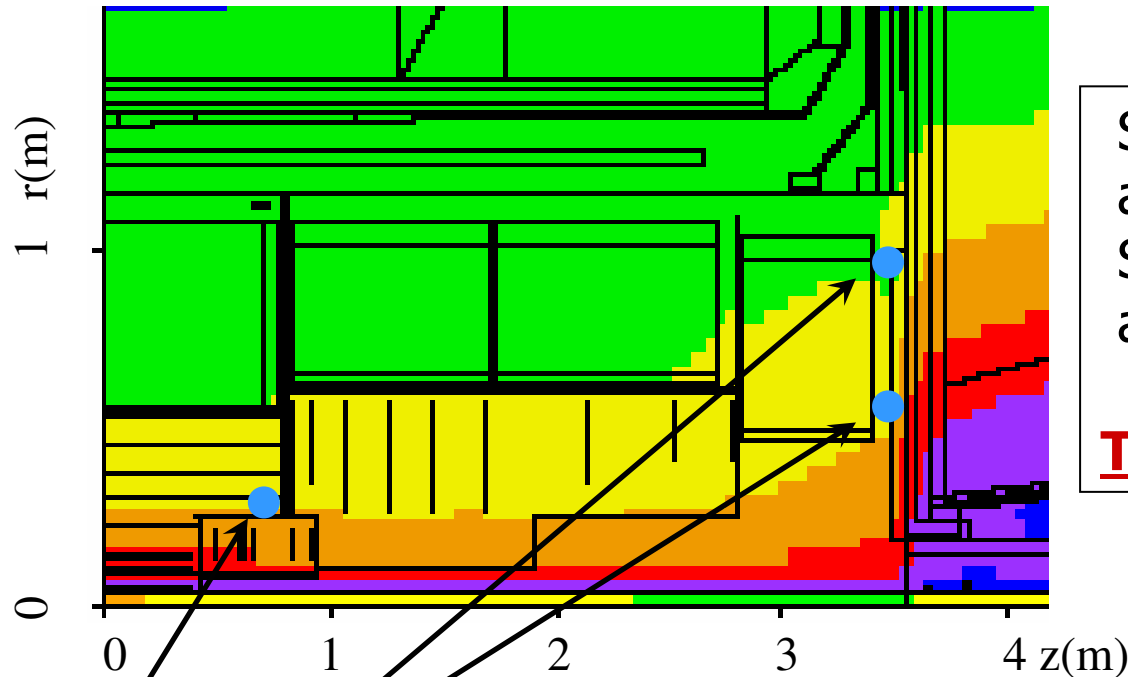
• more information in:

- **EDMS document: *ATL-IC-ES-0017***

- [http://www-f9.ijs.si/~mandic/RADMON/atlas\\_radiation\\_monitor.htm](http://www-f9.ijs.si/~mandic/RADMON/atlas_radiation_monitor.htm)



# Positions of RMSBs in the ID



Side A ( $z > 0$ ):  
 at  $\Phi = 0^\circ$  and  $180^\circ$   
 Side C ( $z < 0$ ):  
 at  $\Phi = 90^\circ$  and  $270^\circ$   
**Total of 12 in the ID**

$r[\text{cm}]$	$z[\text{cm}]$	$\Phi_{\text{eq}}$ [ $10^{14}/\text{m}^2$ ] 10 y (LL y)	$\Phi(E > 20 \text{ MeV})$ [ $10^{14}/\text{cm}^2$ ]	TID[ $10^4 \text{ Gy}$ ] 10 y (LL y)
20-30	80-90	2.33 (0.03)	2.2	14 (0.2)
40-50	340-350	2.35 (0.03)	1.25	6.7 (0.09)
80-90	340-350	1.06 (0.01)	0.41	1.91 (0.03)



## Sensors planned to be used on ID RMSB

Monitor Total Ionizing Dose (TID):

- RADFET's (threshold voltage increase)

Monitor NIEL:

- EPI PIN-diodes (leakage current increase with NIEL)
- PIN diodes under forward bias (resistivity increase with NIEL)

Monitor thermal neutrons (and monitor the damage of ABCD3T input transistor):

- DMILL bipolar transistor from ATMEL (measure decrease of common-emitter current gain (increase of base current at given collector current))

### Temperature control

Temperature should be stable to simplify analysis (annealing...)  
Stabilization achieved by heating sensor boards made of ceramics to few degrees above environment temperature of  $\sim 20^{\circ}\text{C}$ .



# Read-out

## ELMB + DAC boards:

- ELMB available, 64 ADC channels
- DAC board (16 channels) produced and tested

Fully compatible with ATLAS DCS (CAN bus communication)

Compliant with radiation tolerance requirements

## Readout principles

**RADFET, PIN:** current enforced (DAC)-voltage measured (ADC)

**EPI:** current (DAC) converted to voltage (resistor) –  
voltage drop on resistor due to leakage current measured (ADC)

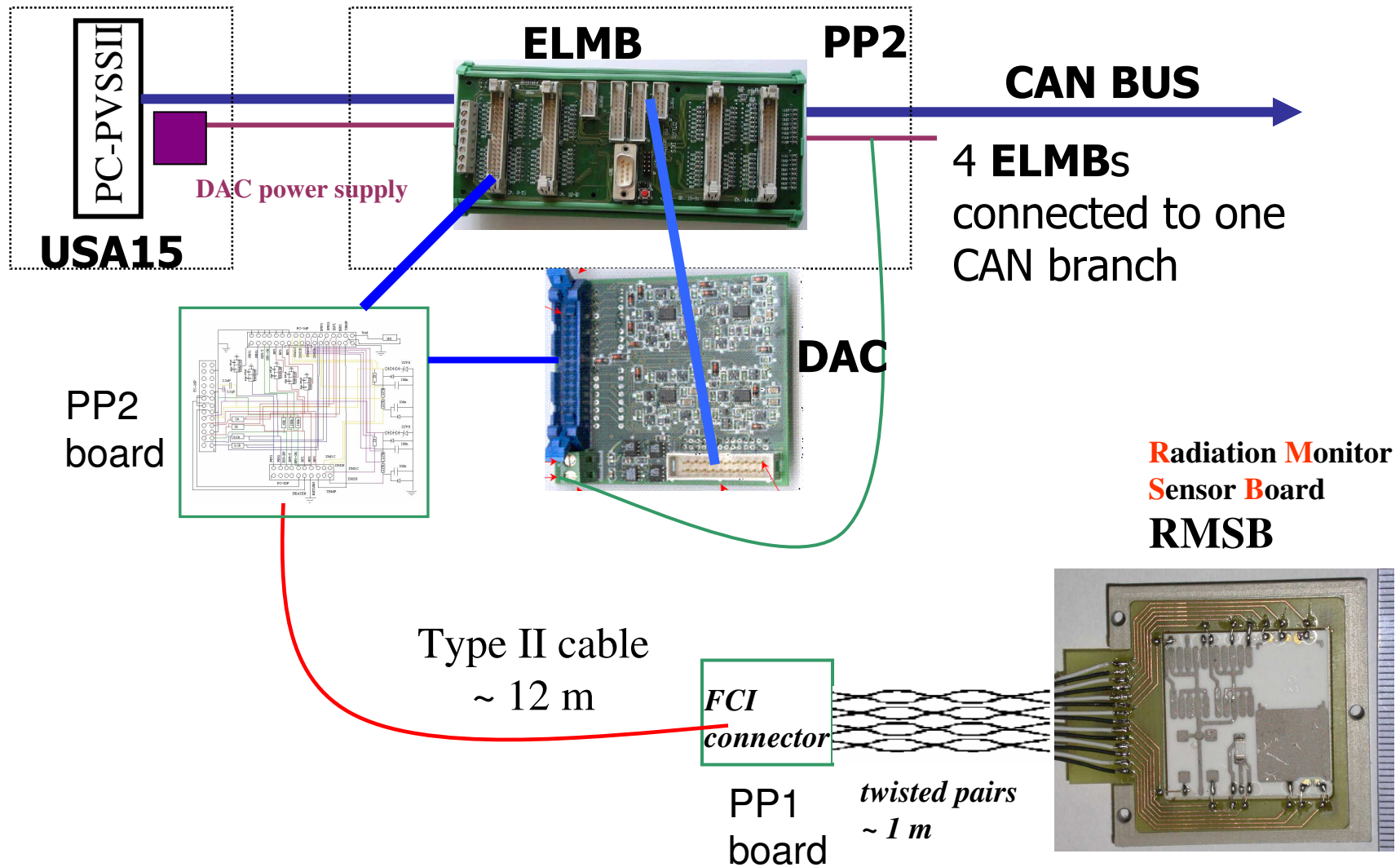
**DMILL:** collector current enforced (DAC) –  
voltage drop on resistor due to base current measured (ADC)

**Maximum voltage of DAC limited to 28 V!**

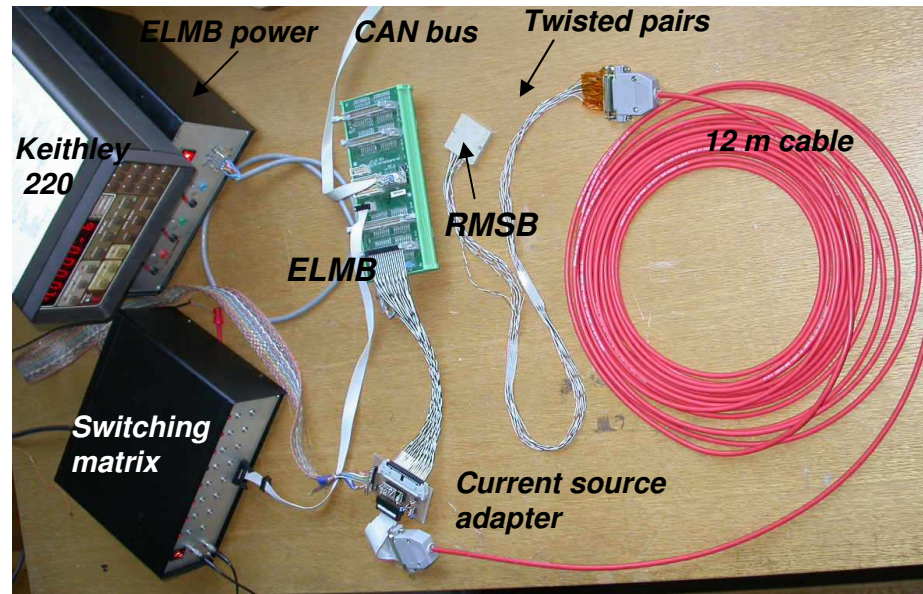
**HEATER:** 4 or more DAC channels connected together



# Schematic view of the Inner Detector monitor



# System test



Aim: determine the sensitivity of the system

- read sensors in certain time intervals
- after 150 hours RMSB exposed to  $^{22}\text{Na}$  source (  $D/t \sim 20 \mu\text{Sv/h}$  )

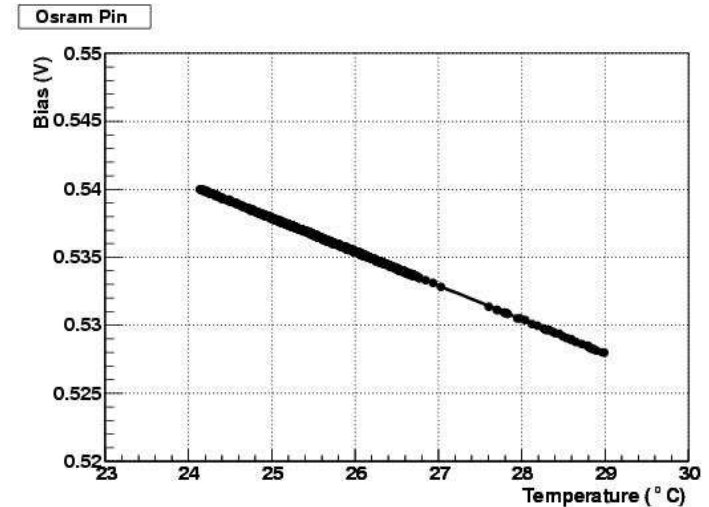
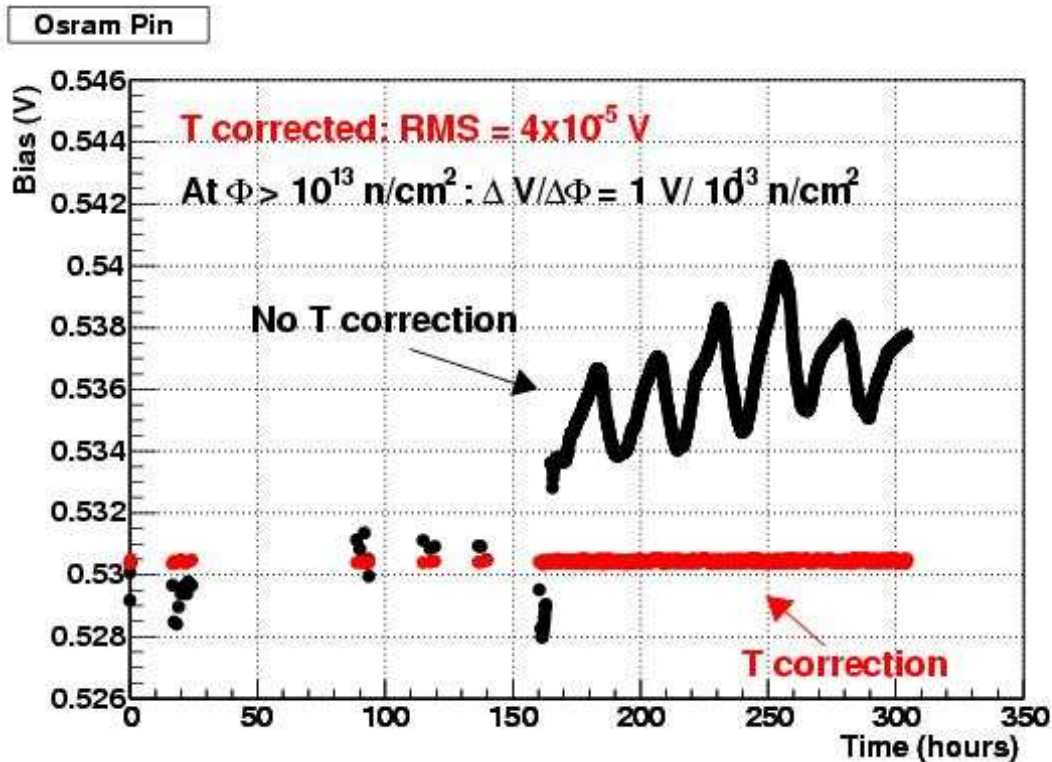


# Osram BPW34F pin diode

Temperature of the RMSB not stabilized

→ correct for temperature variations offline:

Measure bias voltage at forward current  $I_f = 1 \text{ mA}$



Sensitivity:

**BPW34F** ( $\Delta V / \Delta \Phi = 1 \text{ V} / 10^{13} \text{ n/cm}^2$ )  
→ better than  $10^{10} \text{ n/cm}^2$

**CMRP** ( $\Delta V / \Delta \Phi = 1 \text{ V} / 10^{11} \text{ n/cm}^2$ )  
→ better than  $10^8 \text{ n/cm}^2$



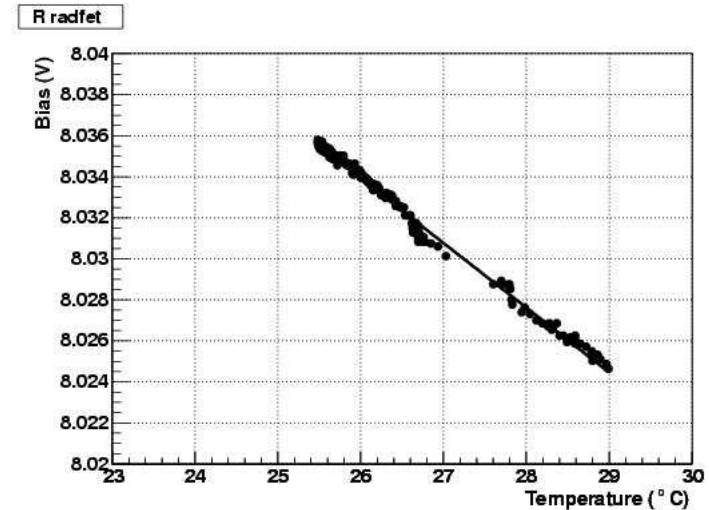
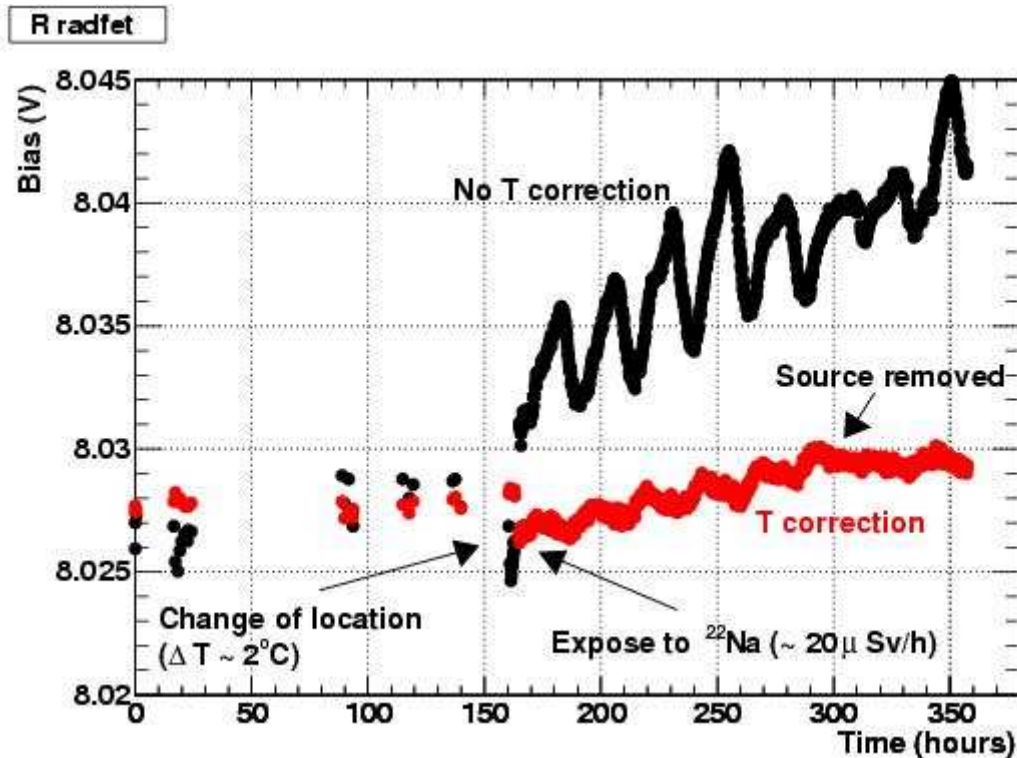


# REM thick oxide RADFET

Temperature of the RMSB not stabilized

→ correct for temperature variations offline:

Measure gate voltage at drain current  $I_d = 160 \mu\text{A}$



Detectable:  $\Delta V \sim 2 \text{ mV}$

LAAS radfets ( $\Delta V/\Delta D \sim 0.5 \text{ V/Gy}$ )  
will be used in ATLAS:

Sensitivity  $\sim 4 \text{ mGy}$





# Monitors for Locations Outside of the Inner Detector

- simpler sensor boards:
  - LAAS radfet + CMRP diode + temperature sensor
  - no temperature stabilization
  - RMSB can be a simple  $\sim 2 \times 2 \text{ cm}^2$  PCB
  - no unprotected wire bonds → no need for housing
- use free channels on existing subdetector's ELMBs

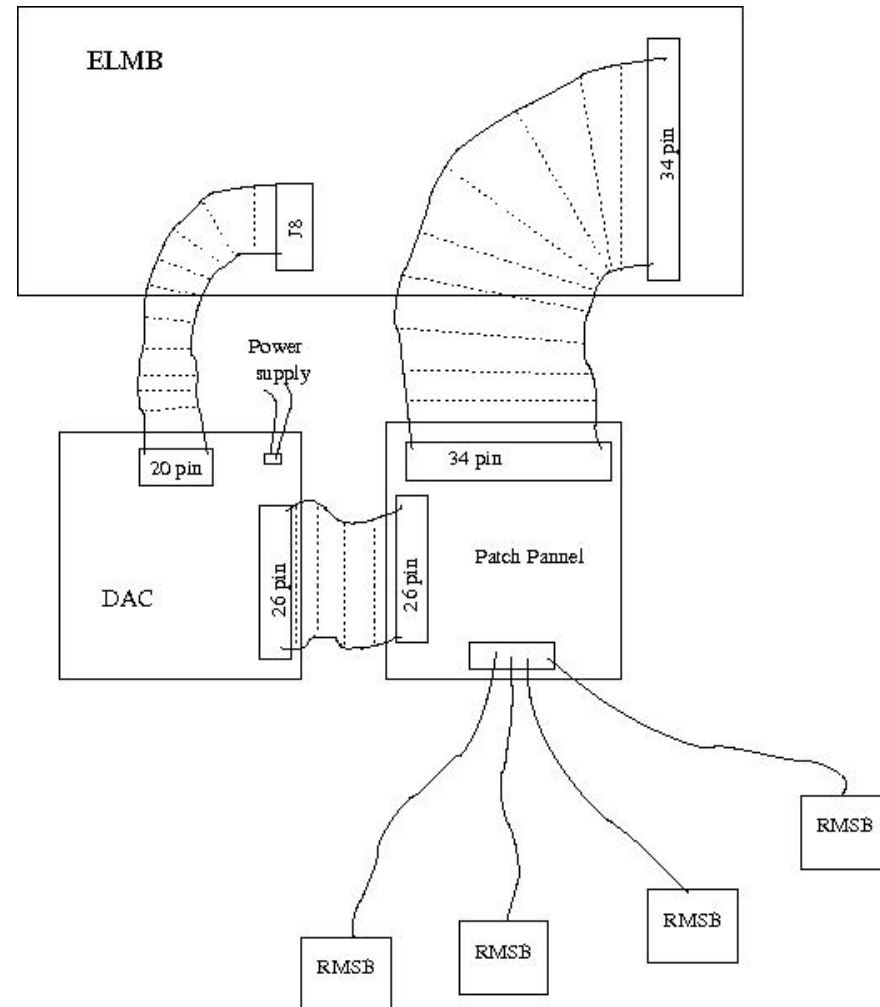
## Cost estimate for the simplified radiation sensor board:

thick oxide radfet	:	1x 60 CHF	= 60
CMRP PIN diode	:	1x120 CHF	= 120
Temperature sensor	:	1x 10 CHF	= 10
DAC (minimum cost)	:	2x22 CHF	= 44 (depends on number of RMSBs per DAC board)
board	:	1x10 CHF	= 10
TOTAL			= 244 CHF



# Scheme of Connections

- use ELMB power lines (12 V) to power DAC → to get  $\sim 10$  V at DAC output
- up to 8 RMSBs can be connected to one DAC board
- each RMSB needs at least 3 ADC channels (max. 5 if DAC output is also monitored)



# Conclusion

- Ljubljana can produce:
  - RMSB boards
  - DAC boards
  - patch pannel boards
- Subdetectors must take care of
  - cabling
  - finding free ELMB channels
  - providing the number of RMSB, DAC and patch-pannel boards as soon as possible

